

SINGLE 2 INPUT POSITIVE NAND GATE

Description

The 74LVCE1G00 is a single 2-input positive NAND gate with a standard totem pole output. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

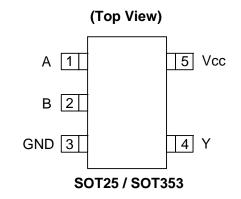
The gate performs the positive Boolean function:

$Y = \overline{A \bullet B} \text{ or } Y = \overline{A} + \overline{B}$

Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
- 200-V Machine Model (A115-A)
- 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25 and SOT353: Assembled with "Green" Molding Compound (No Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)
- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- Wide array of products such as.
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

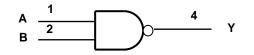


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Pin Descriptions

Pin Name	Pin NO.	Description			
А	1	Data Input			
В	2	Data Input			
GND	3	Ground			
Y	4	Data Output			
Vcc	5	Supply Voltage			

Logic Diagram



Function Table

Inp	Output	
Α	В	Y
Н	Н	L
L	Х	Н
Х	L	Н



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Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
Ι _{ΟΚ}	Output Clamp Current	-50	mA
Ι _Ο	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



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Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit	
		Operating	1.4	5.5	V	
V_{CC}	Operating Voltage	Data retention only	1.2		V	
		$V_{\rm CC} = 1.4$ V to 1.95 V	0.65 X V _{CC}			
N/	Lligh lovel loovet \/eltege	$V_{\rm CC}$ = 2.3 V to 2.7 V	1.7		V	
V _{IH} Hig	High-level Input Voltage	$V_{CC} = 3 V$ to 3.6 V	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 X V _{CC}			
		$V_{\rm CC} = 1.4 \text{ V}$ to 1.95 V		0.35 X V _{CC}		
N/		$V_{\rm CC}$ = 2.3 V to 2.7 V		0.7	V	
VIL	V _{IL} Low-level input voltage	$V_{CC} = 3 V$ to 3.6 V		0.8	V	
		$V_{\rm CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 X V _{CC}		
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{cc}	V	
	High-level output current	Vcc=1.4 V		-3		
		V _{CC} = 1.65 V		-4		
		$V_{CC} = 2.3 V$		-8	m /	
I _{ОН}				-16	mA	
		$V_{CC} = 3 V$		-24		
		$V_{CC} = 4.5 V$		-32		
		Vcc=1.4 V		3		
		V _{CC} = 1.65 V		4		
		$V_{CC} = 2.3 V$		8	mA	
I _{OL}	Low-level output current			16		
		$V_{CC} = 3 V$		24		
		$V_{CC} = 4.5 V$		32		
		$V_{\rm CC} = 1.4$ to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	rate	$V_{\rm CC} = 5 \text{V} \pm 0.5 \text{V}$		5		
T _A	Operating free-air temperature		-40	85	٥C	

Notes: 3. Unused inputs should be held at Vcc or Ground.



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Electrical Characteristics (All typical values are at Vcc = 3.3V, T_A = 25° C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
		I _{OH} = -100μA	1.4 V to 5.5V	$V_{CC} - 0.1$			
		I _{OH} = -3mA	1.4 V	1.05			
		I _{OH} = -4mA	1.65 V	1.2			
V _{OH}	High Level Output Voltage	I _{OH} = -8mA	2.3V	1.9			V
		I _{OH} = -16mA	-3 V	2.4			
		I _{OH} = -24mA	3 V	2.3			
		I _{OH} = -32mA	4.5 V	3.8			
		I _{OL} = 100μA	1.4 V to 5.5V			0.1	
		$I_{OL} = 3mA$	1.4V			.4	
		$I_{OL} = 4mA$	1.65 V			0.45	
V _{OL}	High-level Input Voltage	$I_{OL} = 8mA$	2.3V			0.3	V
		I _{OL} = 16mA	-3 V			0.4	
		$I_{OL} = 24 \text{mA}$	3 V			0.55	
		$I_{OL} = 32 \text{mA}$	4.5			0.55	
I _I	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA
I _{OFF}	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5 V$	0			± 10	μA
I _{CC}	Supply Current	$V_1 = 5.5V \text{ of GND}$ $I_0=0$	1.4 V to 5.5V			10	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} – 0.6 V Other inputs at $V_{CC or}$ GND	3 V to 5.5V			500	μA
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF
٥	Thermal Resistance	SOT25	(Note 4)		204		°C/W
θ_{JA}	Junction-to-Ambient	SOT353	(Note 4)		371		°C/W
٥	Thermal Resistance	SOT25	(Note 4)		52		°C/W
θ_{JC}	Junction-to-Case	SOT353	(Note 4)		143		°C/W

Over recommended free-air temperature range (unless otherwise noted)

Notes: 4. Test condition for SOT25 and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



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Switching Characteristics

Parameter	From (Input)			то	± 0.1V		Vcc = 1.8 V ± 0.15V		Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit
i arameter		(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max			
t _{pd}	A or B	Y	2.2	7.2	1.5	5	0.6	3.5	0.6	3.1	0.7	3	ns		

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter From		то	Vcc = ± 0			: 1.8 V .15V		: 2.5 V).2V		3.3 V .3V		= 5 V).5V	Unit
(Inp	(Input)	Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	•
t _{pd}	A or B	Y	3.1	9	2.1	6.3	1	4.4	0.8	3.8	0.9	3.6	ns

Operating Characteristics

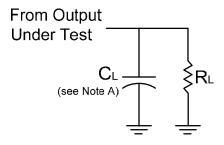
 $T_A = 25 \ ^{o}C$

Р	arameter		Vcc = 1.5 V	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
-	Condition		TYP	ТҮР	ТҮР	ТҮР	TYP	•
C_{pd}	Power dissipation capacitance	f = 10 MHz	22	22	22	23	25	pF

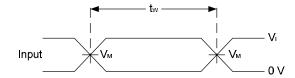


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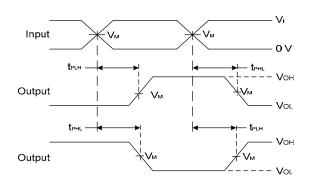
Parameter Measurement Information



Vcc	In	puts	V.	CL	D.	
VCC	VI	t _r /t _f	V _M	υL	RL	
1.5V±0.10V	V _{cc}	≤2ns	V _{CC} /2	15pF	1MΩ	
1.8V±0.15V	V _{cc}	≤2ns	V _{CC} /2	15pF	1MΩ	
2.5V±0.2V	V _{cc}	≤2ns	V _{CC} /2	15pF	1MΩ	
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1MΩ	



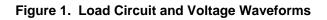
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance.

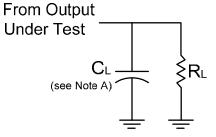
- B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



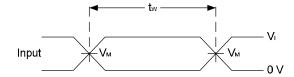


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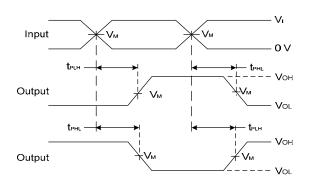
Parameter Measurement Information (Continued)



Vcc	Inp	outs	V _M	CL	RL	
	VI	t _r /t _f	- 101	°L		
1.5V±0.10V	V _{cc}	≤2ns	V _{CC} /2	30pF	1KΩ	
1.8V±0.15V	V _{cc}	≤2ns	V _{CC} /2	30pF	1KΩ	
2.5V±0.2V	V _{cc}	≤2ns	V _{CC} /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω	



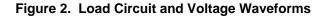
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

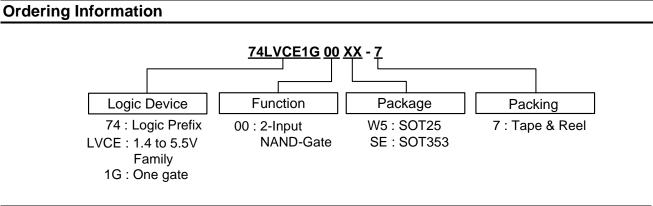
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{PD.}$





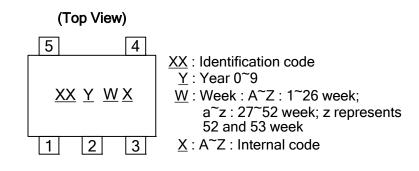
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	Daviaa	Device Package Packaging		7" Tape and Reel		
	Device	Code	(Note 5)	Quantity	Part Number Suffix	
PD,	74LVCE1G00W5-7	W6	SOT25	3000/Tape & Reel	-7	
•	74LVCE1G00SE-7	SE	SOT353	3000/Tape & Reel	-7	

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



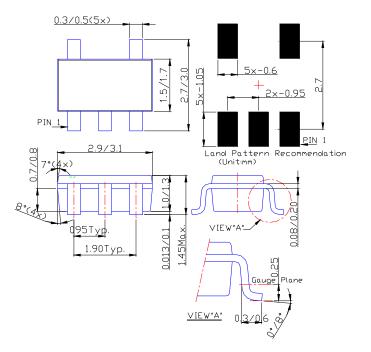
Part Number	Package	Identification Code	
74LVCE1G00W5	SOT25	PS	
74LVCE1G00SE	SOT353	PS	



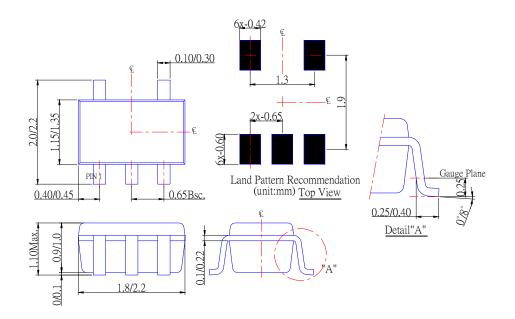
SINGLE 2 INPUT POSITIVE NAND GATE

Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



(2) Package Type: SOT353



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